User Flash Area

Section	Description	Address	# of Bytes	RO or RW	Data Type	FW Type	Default value	Comment
Flash Format Info	Flash Map Version	0x000000	2	READONLY	HEX16	NONE	FLASH_MAP_ID	
	Flash Valid Flag	0x000002	1	READONLY	HEX8	NONE	0xAA	
Board Info	Board Default CAN ID	0x000003	1	READWRITE	HEX8	DECIMAL	0xFE	CAN ID used by J1939
	Board Default Full CAN Device Name	0x000004	8	READWRITE	HEX64	HEX64	0x0000000000000001	Full CAN Device Name
Cell Stack Info	Maximum Cell Voltage	0x00000C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	3.8	Cell max charge cutoff
	Minimum Cell Voltage	0x000010	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1.6	Cell min charge cutoff
	Maximum Charge Voltage	0x000014	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	3.6	Cell max recommended charge cutoff
	Minimum Charge Voltage	0x000018	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	2	Cell min recommended charge cutoff
	Nominal Cell Voltage	0x00001C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	3.3	Cell nominal voltage
	Recommended Charge Current	0x000020	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	5	Cell charge current in Amps
	Recommended Total Charge time	0x000024	2	READWRITE	HEX16	DECIMAL	2700	Cell charge time in seconds at rec. charge current
	Pulse Charge Time	0x000026	2	READWRITE	HEX16	DECIMAL	1000	Charge pulse length in milliseconds
	Pulse Relaxation Time	0x000028	2	READWRITE	HEX16	DECIMAL	3000	Relaxation pulse length in milliseconds
	Number of Cells in Module	0x00002A	1	READWRITE	HEX8	DECIMAL	14	Number of cells in series
	Stack location	0x00002B	1	READWRITE	HEX8	DECIMAL	0xff	Bottom of stack=1; max stack=32; unassigned=0xff
	Max Charge Current	0x00002C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	10	Cell Fast charge current in Amps
	Fast Charge Time	0x000030	2	READWRITE	HEX16	DECIMAL	900	Total charge time at Max Charge Current (seconds)
	Cell Type Code	0x000032	1	READWRITE	HEX8	DECIMAL	0	Cell battery type code assigned by NSC
	Cells in Parallel	0x000033	1	READWRITE	HEX8	DECIMAL	1	Number 0f cells in parallel per series cell
	Hysteresis Voltage	0x000034	2	READWRITE	HEX16	HEX16	10	Hysteresis for ACB voltage in mV
	ACB Voltage Threshold	0x000036	2	READWRITE	HEX16	HEX16	2	Target threshold for ACB (in mV) - ACB stops within target
	Cell Capacity	0x000038	2	READWRITE	HEX16	DECIMAL	2600	Cell capacity in mAh (GUI parameter until SOC is ready)
Hardware Info	Board Hardware Version	0x000040	2	READWRITE	HEX16	ASCII	A4	PCB rev
	Board Rework Level	0x000042	1	READWRITE	HEX8	DECIMAL	1	Rework level of board
	Board Serial Number	0x000043	8	READONLY	HEX64	HEX64	0x0000000000000001	Serial number
	CAN Master/Slave Control	0x00004B	1	READWRITE	HEX8	DECIMAL	0	Master=1 and Slave=0 Master provides heartbeat sync pulse
	Device Type	0x00004C	1	READWRITE	HEX8	DECIMAL	0	Type of device: 1=Cheetah, all others undefined
	Original Flash Map	0x00004D	2	READWRITE	HEX16	DECIMAL	0xffff	Flash Map ID when manufacturer's data is first written
Current Setpoint Info	Upper Tigon Charge Current Setpoint	0x000100	2	READWRITE	HEX16	DECIMAL	0x026c	Voltage=(value/1023)*3.3 2V yields 5A
	Upper Tigon Discharge Current Setpoint	0x000102	2	READWRITE	HEX16	DECIMAL	0x026c	Voltage=(value/1023)*3.3 2V yields 5A
	Lower Tigon Charge Current Setpoint	0x000104	2	READWRITE	HEX16	DECIMAL	0x026c	Voltage=(value/1023)*3.3 2V yields 5A
	Lower Tigon Discharge Current Setpoint	0x000106	2	READWRITE	HEX16	DECIMAL	0x026c	Voltage=(value/1023)*3.3 2V yields 5A
AFE Calibration Gain Info	Cell 1 Gain	0x000108	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 2 Gain	0x00010C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 3 Gain	0x000110	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 4 Gain	0x000114	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 5 Gain	0x000118	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 6 Gain	0x00011C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 7 Gain	0x000120	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 8 Gain	0x000124	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 9 Gain	0x000128	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 10 Gain	0x00012C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 11 Gain	0x000130	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 12 Gain	0x000134	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 13 Gain	0x000138	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 14 Gain	0x00013C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
AFE Calibration Offset Info	Cell 1 Offset	0x000140	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.026	
	Cell 2 Offset	0x000144	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	-0.033	
	Cell 3 Offset	0x000148	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	-0.027	
	Cell 4 Offset	0x00014C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	-0.009	
	Cell 5 Offset	0x000150	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	-0.008	
	Cell 6 Offset	0x000154	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.017	
	Cell 7 Offset	0x000158	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	-0.013	
	Cell 8 Offset	0x00015C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	-0.023	
	Cell 9 Offset	0x000160	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.041	
	Cell 10 Offset	0x000164	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	-0.007	
	Cell 11 Offset	0x000168	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	-0.004	
	Cell 12 Offset	0x00016C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	-0.031	
	Cell 13 Offset	0x000170	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.01	
	Cell 14 Offset	0x000174	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	-0.002	
Temperature Data	Temp Chan 1 Gain	0x000178	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Temp Chan 2 Gain	0x00017C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Temp Chan 3 Gain	0x000180	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Temp Chan 4 Gain	0x000184	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Temp Chan 5 Gain	0x000188	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Temp Chan 6 Gain	0x00018C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Temp Chan 7 Gain	0x000190	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Temp Chan 8 Gain	0x000194	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
Temperature Offset Info	Temp Chan 1 Offset	0x000198	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.001	
	Temp Chan 2 Offset	0x00019C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.001	
	Temp Chan 3 Offset	0x0001A0	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.001	
	Temp Chan 4 Offset	0x0001A4	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.001	
	Temp Chan 5 Offset	0x0001A8	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.001	
	Temp Chan 6 Offset	0x0001AC	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.001	
	Temp Chan 7 Offset	0x0001B0	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.001	
	Temp Chan 8 Offset	0x0001B4	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.001	
Data Reporting Rates	AFE Report Rate	0x0001B8	2	READWRITE	HEX16	DECIMAL	0x03e8	Rate in milliSeconds
	Temperature Report Rate	0x0001BA	2	READWRITE	HEX16	DECIMAL	0x03e8	Rate in milliSeconds
	Max Temperature	0x0001BC	2	READWRITE	HEX16	DECIMAL	0x0fff	Over temperature setpoint
	Min Temperature	0x0001BE	2	READWRITE	HEX16	DECIMAL	0x0000	Under temperature setpoint (missing sensor?)
	AFE Oversamples	0x0001C0	1	READWRITE	HEX8	DECIMAL	32	Number of AFE oversamples per report period
Tigon Current Gain Calibration Info	Upper Tigon Charge Current Gain	0x000200	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Upper Tigon Discharge Current Gain	0x000204	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Lower Tigon Charge Current Gain	0x000208	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Lower Tigon Discharge Current Gain	0x00020C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
Tigon Current Offset Calibration Info	Upper Tigon Charge Current Offset	0x000210	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0	Offset in Amps
	Upper Tigon Discharge Current Offset	0x000214	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0	Offset in Amps
	Lower Tigon Charge Current Offset	0x000218	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0	Offset in Amps
	Lower Tigon Discharge Current Offset	0x00021C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0	Offset in Amps

Factory Default Flash Area

Section	Description	Address	# of Bytes	RO or RW	Data Type	FW Type	Default value	Comment
Flash Format Info	Flash Map version	0x000800	2	READONLY	HEX16	NONE	FLASH_MAP_ID	
	Flash Valid Flag	0x000802	1	READONLY	HEX8	NONE	0xAA	
Board Info	Board Default CAN ID	0x000803	1	READWRITE	HEX8	DECIMAL	0xFE	CAN ID used by J1939
	Board Default Full CAN Device Name	0x000804	8	READWRITE	HEX64	HEX64	0x0000000000000001	Full CAN Device Name
Cell Stack Info	Maximum Cell Voltage	0x00080C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	3.8	Cell max charge cutoff
	Minimum Cell Voltage	0x000810	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1.6	Cell min charge cutoff
	Maximum Charge Voltage	0x000814	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	3.6	Cell max recommended charge cutoff
	Minimum Charge Voltage	0x000818	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	2	Cell min recommended charge cutoff
	Nominal Cell Voltage	0x00081C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	3.3	Cell nominal voltage
	Recommended Charge Current	0x000820	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	5	Cell charge current in Amps
	Recommended Total Charge time	0x000824	2	READWRITE	HEX16	DECIMAL	2700	Cell charge time in seconds at rec. charge current
	Pulse Charge Time	0x000826	2	READWRITE	HEX16	DECIMAL	1000	Charge pulse length in milliseconds
	Pulse Relaxation Time	0x000828	2	READWRITE	HEX16	DECIMAL	3000	Relaxation pulse length in milliseconds
	Number of Cells in Module	0x00082A	1	READWRITE	HEX8	DECIMAL	14	Number of cells in series
	Stack location	0x00082B	1	READWRITE	HEX8	DECIMAL	0xff	Bottom of stack=1; max stack=32; unassigned=0xff
	Max Charge Current	0x00082C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	10	Cell Fast charge current in Amps
	Fast Charge Time	0x000830	2	READWRITE	HEX16	DECIMAL	900	Total charge time at Max Charge Current (seconds)
	Cell Type Code	0x000832	1	READWRITE	HEX8	DECIMAL	0	Cell battery type code assigned by NSC
	Cells in Parallel	0x000833	1	READWRITE	HEX8	DECIMAL	1	Number 0f cells in parallel per series cell
	Hysteresis Voltage	0x000834	2	READWRITE	HEX16	HEX16	10	Hysteresis for ACB voltage in mV
	ACB Voltage Threshold	0x000836	2	READWRITE	HEX16	HEX16	2	Target threshold for ACB (in mV) - ACB stops within target
	Cell Capacity	0x000838	2	READWRITE	HEX16	DECIMAL	2600	Cell capacity in mAh (GUI parameter until SOC is ready)
Hardware Info	Board Hardware Version	0x000840	2	READWRITE	HEX16	ASCII	A4	PCB rev
	Board Rework Level	0x000842	1	READWRITE	HEX8	DECIMAL	1	Rework level of board
	Board Serial Number	0x000843	8	READONLY	HEX64	HEX64	0x0000000000000001	Serial number
	CAN Master/Slave Control	0x00084B	1	READWRITE	HEX8	DECIMAL	0	Master=1 and Slave=0 Master provides heartbeat sync pulse
	Device Type	0x00084C	1	READWRITE	HEX8	DECIMAL	0	Type of device: 1=Cheetah, all others undefined
	Original Flash Map	0x00084D	2	READWRITE	HEX16	DECIMAL	0xffff	Flash Map ID when manufacturer's data is first written
Current Setpoint Info	Upper Tigon Charge Current Setpoint	0x000900	2	READWRITE	HEX16	DECIMAL	0x026c	Voltage=(value/1023)*3.3 2V yields 5A
	Upper Tigon Discharge Current Setpoint	0x000902	2	READWRITE	HEX16	DECIMAL	0x026c	Voltage=(value/1023)*3.3 2V yields 5A
	Lower Tigon Charge Current Setpoint	0x000904	2	READWRITE	HEX16	DECIMAL	0x026c	Voltage=(value/1023)*3.3 2V yields 5A
	Lower Tigon Discharge Current Setpoint	0x000906	2	READWRITE	HEX16	DECIMAL	0x026c	Voltage=(value/1023)*3.3 2V yields 5A
AFE Calibration Gain Info	Cell 1 Gain	0x000908	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 2 Gain	0x00090C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 3 Gain	0x000910	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 4 Gain	0x000914	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 5 Gain	0x000918	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 6 Gain	0x00091C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 7 Gain	0x000920	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 8 Gain	0x000924	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 9 Gain	0x000928	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 10 Gain	0x00092C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 11 Gain	0x000930	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 12 Gain	0x000934	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 13 Gain	0x000938	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Cell 14 Gain	0x00093C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
AFE Calibration Offset Info	Cell 1 Offset	0x000940	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT		*Determined on tester
	Cell 2 Offset	0x000944	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT		*Determined on tester
	Cell 3 Offset	0x000948	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT		*Determined on tester
	Cell 4 Offset	0x00094C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT		*Determined on tester
	Cell 5 Offset	0x000950	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT		*Determined on tester
	Cell 6 Offset	0x000954	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT		*Determined on tester
	Cell 7 Offset	0x000958	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT		*Determined on tester
	Cell 8 Offset	0x00095C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT		*Determined on tester
	Cell 9 Offset	0x000960	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT		*Determined on tester
	Cell 10 Offset	0x000964	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT		*Determined on tester
	Cell 11 Offset	0x000968	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT		*Determined on tester
	Cell 12 Offset	0x00096C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT		*Determined on tester
	Cell 13 Offset	0x000970	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT		*Determined on tester
	Cell 14 Offset	0x000974	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT		*Determined on tester
Temperature Data	Temp Chan 1 Gain	0x000978	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Temp Chan 2 Gain	0x00097C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Temp Chan 3 Gain	0x000980	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Temp Chan 4 Gain	0x000984	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Temp Chan 5 Gain	0x000988	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Temp Chan 6 Gain	0x00098C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Temp Chan 7 Gain	0x000990	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Temp Chan 8 Gain	0x000994	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
Temperature Offset Info	Temp Chan 1 Offset	0x000998	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.001	
	Temp Chan 2 Offset	0x00099C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.001	
	Temp Chan 3 Offset	0x0009A0	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.001	
	Temp Chan 4 Offset	0x0009A4	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.001	
	Temp Chan 5 Offset	0x0009A8	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.001	
	Temp Chan 6 Offset	0x0009AC	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.001	
	Temp Chan 7 Offset	0x0009B0	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.001	
	Temp Chan 8 Offset	0x0009B4	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0.001	
Data Reporting Rates	AFE Report Rate	0x0009B8	2	READWRITE	HEX16	DECIMAL	0x03e8	Rate in milliSeconds
	Temperature Report Rate	0x0009BA	2	READWRITE	HEX16	DECIMAL	0x03e8	Rate in milliSeconds
	Max Temperature	0x0009BC	2	READWRITE	HEX16	DECIMAL	0x0fff	Over temperature setpoint
	Min Temperature	0x0009BE	2	READWRITE	HEX16	DECIMAL	0x0000	Under temperature setpoint (missing sensor?)
	AFE Oversamples	0x0009C0	1	READWRITE	HEX8	DECIMAL	32	Number of AFE oversamples per report period
Tigon Current Gain Calibration Info	Upper Tigon Charge Current Gain	0x000A00	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Upper Tigon Discharge Current Gain	0x000A04	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Lower Tigon Charge Current Gain	0x000A08	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
	Lower Tigon Discharge Current Gain	0x000A0C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	1	
Tigon Current Offset Calibration Info	Upper Tigon Charge Current Offset	0x000A10	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0	Offset in Amps
	Upper Tigon Discharge Current Offset	0x000A14	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0	Offset in Amps
	Lower Tigon Charge Current Offset	0x000A18	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0	Offset in Amps
	Lower Tigon Discharge Current Offset	0x000A1C	4	READWRITE	IEEE_FLOAT32	SIGNED_FLOAT	0	Offset in Amps